

Ming Gao

List of Publications by Citations

Source: <https://exaly.com/author-pdf/3099652/ming-gao-publications-by-citations.pdf>

Version: 2024-04-29

This document has been generated based on the publications and citations recorded by exaly.com. For the latest version of this publication list, visit the link given above.

The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

17
papers

112
citations

6
h-index

10
g-index

19
ext. papers

128
ext. citations

4.2
avg, IF

2.22
L-index

#	Paper	IF	Citations
17	Effect of post-annealing on the properties of thermally evaporated molybdenum oxide films: Interdependence of work function and oxygen to molybdenum ratio. <i>Materials Science in Semiconductor Processing</i> , 2018 , 75, 166-172	4.3	26
16	Bifunctional Hybrid a-SiO (Mo) Layer for Hole-Selective and Interface Passivation of Highly Efficient MoO ₃ /a-SiO (Mo)/n-Si Heterojunction Photovoltaic Device. <i>ACS Applied Materials & Interfaces</i> , 2018 , 10, 27454-27464	9.5	21
15	Effective Passivation and Tunneling Hybrid a-SiO(In) Layer in ITO/n-Si Heterojunction Photovoltaic Device. <i>ACS Applied Materials & Interfaces</i> , 2017 , 9, 17565-17575	9.5	14
14	Elucidating the evolution of the current-voltage characteristics of planar organometal halide perovskite solar cells to an S-shape at low temperature. <i>Solar Energy Materials and Solar Cells</i> , 2016 , 157, 981-988	6.4	12
13	Variation of passivation behavior induced by sputtered energetic particles and thermal annealing for ITO/SiO _x /Si system. <i>Chinese Physics B</i> , 2017 , 26, 045201	1.2	9
12	Hydrogen-free synthesis of graphene/graphitic films directly on Si substrate by plasma enhanced chemical vapor deposition. <i>Journal of Materials Science: Materials in Electronics</i> , 2015 , 26, 1485-1493	2.1	9
11	Electronic structure of molybdenum-involved amorphous silica buffer layer in MoO ₃ /n-Si heterojunction. <i>Applied Surface Science</i> , 2019 , 473, 20-24	6.7	5
10	Questing and the application for silicon based ternary compound within ultra-thin layer of SIS intermediate region. <i>Applied Surface Science</i> , 2016 , 388, 57-63	6.7	4
9	Hydrogen-free synthesis of few-layer graphene film on different substrates by plasma enhanced chemical vapor deposition. <i>Journal of Materials Science: Materials in Electronics</i> , 2015 , 26, 6961-6969	2.1	2
8	Role of nuclei in controllable MoS ₂ growth by modified chemical vapor deposition. <i>Journal of Materials Science: Materials in Electronics</i> , 2018 , 29, 7425-7434	2.1	2
7	?????????????????????. <i>Chinese Science Bulletin</i> , 2015 , 60, 1841-1848	2.9	2
6	CVD Polycrystalline Graphene as Sensing Film of Extended-Gate ISFET for Low-Drift pH Sensor. <i>Journal of the Electrochemical Society</i> ,	3.9	2
5	Improvement of the performance of ITO/a-SiO _x /n-Si device by controllable sputtering power and reducible interface states. <i>Materials Science in Semiconductor Processing</i> , 2020 , 105, 104702	4.3	2
4	The hole transport mechanism of MoO ₃ /a-Si: H(i)/n-Si heterojunction photovoltaic devices: the source of the S-shaped behavior. <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 425302	3	1
3	First principle study of formation mechanism of molybdenum-doped amorphous silica in MoO ₃ /Si interface. <i>Wuli Xuebao/Acta Physica Sinica</i> , 2019 , 68, 103101	0.6	1
2	Temperature-dependent nonmonotonous evolution of excitonic blue luminescence and Stokes shift in chlorine-based organometallic halide perovskite film. <i>Applied Physics Letters</i> , 2020 , 116, 072104	3.4	0
1	Low Drift Reference-less ISFET Comprising Two Graphene Films with Different Engineered Sensitivities. <i>ACS Applied Electronic Materials</i> , 2022 , 4, 416-423	4	0

